Product data sheet

1. General description

Ultrafast dual epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	neter Conditions Values					Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			2	200		V
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2		2	20		А
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s;		().2		А
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	8				kV
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; per diode	20			А	
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125			А	
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137				А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics		,				
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V
Dynamic	characteristics				'		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5		-	20	25	ns
		I_F = 0.5 A to I_R = 1 A; T_j = 25 °C; measured at I_R = 0.25 A; step recovery; Fig. 6		-	10	20	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	7 7	[5]
3	A2	anode 2		A1 A2
mb	К	mounting base; cathode		K sym125
			1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV32E-200	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV32E-200	BYV32E-200

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V_R	reverse voltage	DC	200	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; Fig 1; Fig 2	20	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \ \mu s$; $T_{mb} \le 115 \ ^{\circ}C$; per diode	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	А
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	А
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s; per diode	0.2	А
I _{RSM}	non-repetitive peak reverse current	t_p = 100 μ s; per diode	0.2	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C
V _{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k Ω	8	kV

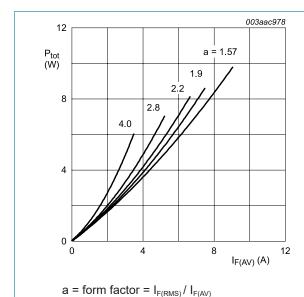
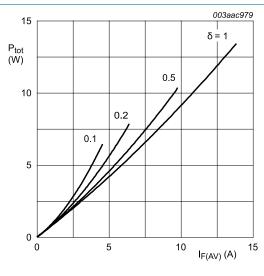


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	60	-	K/W

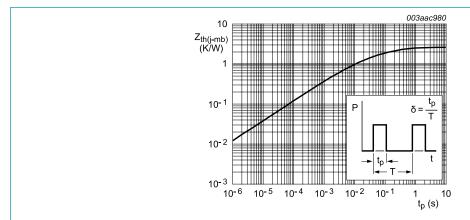


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

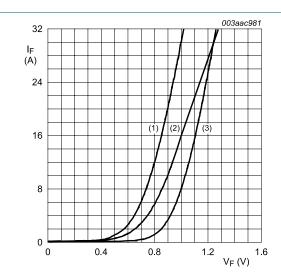
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
V _F	forward voltage	forward voltage $I_F = 8 \text{ A}; T_j = 150 \text{ °C}; Fig. 4$		-	0.72	0.85	V
		I _F = 20 A; T _j = 25 °C		-	1	1.15	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C		-	6	30	μΑ
		V _R = 200 V; T _j = 100 °C		-	0.2	0.6	mA
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}$		-	8	12.5	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; } Fig. 5$		-	20	25	ns
		I_F = 0.5 A to I_R = 1 A; T_j = 25 °C; measured at I_R = 0.25 A; step recovery; Fig. 6		-	10	20	ns
V _{FR}	forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 10 \text{ A}/\mu\text{s}; T_j = 25 °C; Fig. 7$		-	-	1	V

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(2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

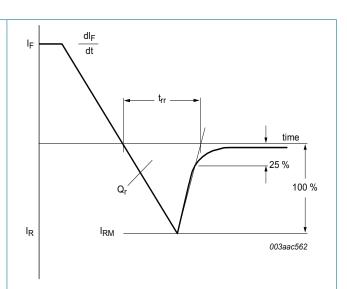


Fig. 5. Reverse recovery definitions; ramp recovery



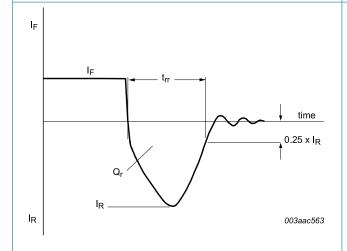


Fig. 6. Reverse recovery definitions; step recovery

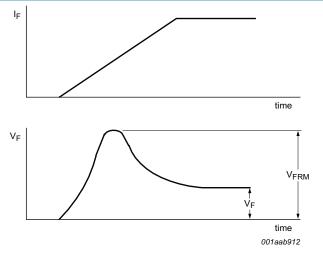
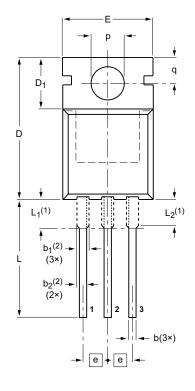


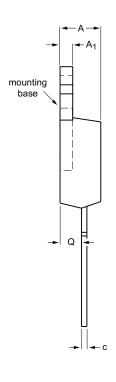
Fig. 7. Forward recovery definitions

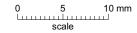
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- ${\it 1. Lead shoulder designs may vary.}\\$
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

BYV32E-200

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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYV32E-200 v.5	20180307	Product specification	-	BYV32E-200_4			
Modifications:	Change from NXP vei	rsion to WeEn version					
BYV32E-200_4	20090227 Product specification - BYV32E_SE						
Modifications:	guidelines of NXP S • Legal texts have be • Package outline upo	en adapted to the new compa	ny name where appro	opriate.			
BYV32E_SERIES_3	20010301	Product specification	-	BYV32E_SERIES_2			
BYV32E_SERIES_2	19980701	Product specification	-	BYV32EB_SERIES_1			
BYV32EB_SERIES_1	19960801	Product specification	-	-			

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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 7 March 2018

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